
Appendix A: List of Papers

A.1 Archival journal articles

1. *Observation of 0.7eV electron trap in dilute GaAsN layers grown by Liquid Phase Epitaxy*

S.Dhar, **N.Halder**, J.Kumar, B.M. Arora

Applied Physics Letters

August 9, 2004 – Volume 85, Issue 6, pp. 964-966

2. *Detailed studies on the origin of nitrogen-related electron traps in dilute GaAsN layers grown by liquid phase epitaxy*

S.Dhar, **N.Halder**, A.Mondal, Bhavtosh Bansal and B.M.Arora

Semiconductor Science and Technology

December 2005 -Volume20, Issue 12, pp. 1168-1172.

3. *Investigation of Deep Level Traps in Dilute GaAsN Layers Grown by Liquid Phase Epitaxy*

S.Dhar, **N.Halder**, A.Mondal

accepted for publication on December, 2005, in the Elsevier Journal “*Thin Solid Films*”

A.2 Conference / Symposium presentations

1. *Deep levels in InGaP layers doped with Fe.*

S.Dhar and **N.Halder**.

XII International Workshop on the Physics of Semiconductor Devices (IWPSD-03),

Madras IIT, Chennai (2003).

2. *Rare-earth and Transition metal doped InGaP: Growth and Characterization.*

S.Dhar and **N.Halder**.

International conference on Communication, Device and Intelligent Systems, Jadavpur University, Calcutta (2004).

3. *Growth of Dilute Nitrides by Liquid Phase Epitaxy.*

S.Dhar, **N.Halder**, J.Kumar.

International conference on Communication, Device and Intelligent Systems, Jadavpur University, Calcutta (2004).

4. Dilute GaAsN layers grown by liquid phase epitaxy.

N.Halder and S.Dhar.

International conference on Computers and Devices for Communication, University of Calcutta, Kolkata (2004).

5. Liquid Phase Epitaxial Growth and Characterization of Dilute III-V Nitrides.

S.Dhar, **N.Halder**, J.Kumar, B.M.Arora.

International conference on Optoelectronics Technology, Jalgaon, North Maharashtra University (2004).

6. Dilute GaAsN layers grown by Liquid Phase Epitaxy

N.Halder

XVII Young Physicists' Colloquium of The Indian Physical Society (YPC – 2004), Saha Inst. of Nuclear Physics, Kolkata (2004).

7. Nitrogen – related Deep Levels in Dilute III-V Nitrides Grown by Liquid Phase Epitaxy

S.Dhar, **N.Halder**, A.Mondal

Seventh International Conference on Optoelectronics, Fiber Optics and Photonics (PHOTONICS-2004), Kochin University Kochi. (2004)

8. Investigation of Deep Level Traps in Dilute GaAsN Layers Grown by Liquid Phase Epitaxy

S.Dhar, **N.Halder**, A.Mondal

3rd International Conference on Materials for Advanced Technologies (ICMAT-2005), Singapore (3-8 July, 2005).

9. Nitrogen-related deep levels in dilute GaAsN layers grown by liquid phase epitaxy

N.Halder

Young Scientists' Colloquium 2005, Material Research Society of India (MRSI, Kolkata Chapter), Saha Institute of Nuclear Physics, Kolkata (July 08, 2005).

10. Liquid Phase Epitaxial growth of Fe-doped and Er-gettered InGaP layers

N.Halder

Presented in *One day seminar on "Material Physics"* organized by Material Research Society of India (Kolkata Chapter) and The West Bengal Academy of Science and Technology to commemorate The World Year of Physics, Saha Institute Auditorium, SINP, Kolkata. (19 th September, 2005)

11. Characteristics of dilute GaAsN layers grown by liquid phase epitaxy

N. Halder, A. Mondal, and S. Dhar

accepted for presentation in the *"International Conference on Electronic and Photonic Materials, Devices and Systems (EPMDS-2006)*, University of Calcutta, Kolkata (January 4-6, 2006)

A.2 Papers not related to the thesis

1. *Characteristics of Metalorganic Vapor Phase Epitaxial $In_{0.49}Ga_{0.51}P$ grown on Liquid Phase Epitaxial $In_{0.49}Ga_{0.51}P/GaAs$.*

S.Dhar, Sarani Basu, **N.Halder**, B.M.Arora.

Sixth International Conference on Optoelectronics, Fiber Optics and Photonics (PHOTONICS-2002), TIFR, Mumbai, India (2002)

2. *Photoemission spectroscopy of Si-implanted GaN*

S.Dhar, Sarani Basu, **N.Halder**

XII International Workshop on the Physics of Semiconductor Devices (IWPSD-03), Madras IIT, Chennai (2003).

3. *Transport properties of n-type GaAs from the analysis of temperature dependent capacitance voltage technique*

Ashok Rao, Kaustav Chakraborty, Rema Bhattacharya, **Nilanjan Halder**.

Indian Science Congress (2003).

4. *Er Gettering of Impurities in GaSb Layers Grown by Liquid Phase Epitaxy*

S.Dhar, A.Mondal, **N.Halder**

Seventh International Conference on Optoelectronics, Fiber Optics and Photonics (PHOTONICS-2004), Kochin University, Kochi. (2004)

5. *Structural, optical and transport properties of ZnO Thin Films*

R.Chandramohan, L.S.Hsu, V.N.Mani, S.Dhar, **N.Halder**

3rd International Conference on Materials for Advanced Technologies (ICMAT-2005), Singapore (3-8 July, 2005).

6. *Growth and characterization of dilute GaSbN and InGaAsSbN layers*

A. Modal, **N. Halder**, and S. Dhar

accepted for presentation in the "*International Conference on Electronic and Photonic Materials, Devices and Systems (EPMDS-2006)*", University of Calcutta, Kolkata (January 4-6, 2006)